

Chapter 3 Transmission Lines and Waveguides

3.1 General solutions for TEM, TE and TM waves
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TEM mode, higher order mode effect

3.7 stripline (TEM line)
conformal mapping solution, electrostatic solution

3.8 Microstrip (quasi-TEM line)
 ϵ_{eff} concept, conformal mapping solution, electrostatic
solution

3.11 Summary of transmission lines and waveguides

3.1 General solutions for TEM, TE and TM waves

- Procedure to analyze a TEM ($E_z, H_z=0$) line

1) solve $\Phi(x, y)$ from Laplace's equation $\nabla_t^2 \Phi(x, y) = 0$

2) apply B.C. $\rightarrow \Phi(x, y)$

3) $\bar{e}(x, y) = -\nabla_t \Phi(x, y) \rightarrow \bar{E}^+(x, y, z) = \bar{e}(x, y) e^{-j\beta z}$

$$\bar{h}(x, y) = \frac{1}{Z_{TEM}} \hat{z} \times \bar{e}(x, y), Z_{TEM} = \frac{E_x^+}{H_y^+} = \eta \rightarrow \bar{H}^+(x, y, z) = \bar{h}(x, y) e^{-j\beta z}$$

4) $V^+ = \Phi_1 - \Phi_2 = \int_1^2 \bar{E}^+ \bullet d\bar{l}, I^+ = \oint \bar{H}^+ \bullet d\bar{l}$

$$5) v_p = \frac{c}{\sqrt{\epsilon_r}}, \quad \beta = \frac{\omega}{v_p} = \omega \sqrt{\mu \epsilon}, \quad Z_o = \frac{V^+}{I^+} = \sqrt{\frac{L}{C}} = \frac{\sqrt{LC}}{C} = \frac{1}{v_p C}$$

- Procedure to analyze a TE ($E_z=0$) or TM ($H_z=0$) line

1) solve $h_z(x, y)$ from Helmholtz equation $(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + k_c^2) h_z(x, y) = 0$: TE case

solve $e_z(x, y)$ from Helmholtz equation $(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + k_c^2) e_z(x, y) = 0$: TM case

2) apply B.C. to find k_c

3) $H_z^+(x, y, z) = h_z(x, y)e^{-j\beta z}$

$$H_x^+ = \frac{-j\beta}{k_c^2} \frac{\partial H_z^+}{\partial x}, H_y^+ = \frac{-j\beta}{k_c^2} \frac{\partial H_z^+}{\partial y}, E_x^+ = \frac{-j\omega\mu}{k_c^2} \frac{\partial H_z^+}{\partial y}, H_y^+ = \frac{j\omega\mu}{k_c^2} \frac{\partial H_z^+}{\partial x} : \text{TE case}$$

$$E_z^+(x, y, z) = e_z(x, y)e^{-j\beta z}$$

$$H_x^+ = \frac{j\omega\varepsilon}{k_c^2} \frac{\partial E_z^+}{\partial y}, H_y^+ = \frac{-j\omega\varepsilon}{k_c^2} \frac{\partial E_z^+}{\partial x}, E_x^+ = \frac{-j\beta}{k_c^2} \frac{\partial E_z^+}{\partial x}, H_y^+ = \frac{-j\beta}{k_c^2} \frac{\partial E_z^+}{\partial y} : \text{TM case}$$

4) $\beta = \sqrt{k^2 - k_c^2}, Z_{TM} (= \frac{E_x^+}{H_y^+}) = \frac{\beta}{\omega\varepsilon} = \frac{\beta\eta}{k}, Z_{TE} (= \frac{E_x^+}{H_y^+}) = \frac{\omega\mu}{\beta} = \frac{k\eta}{\beta}$

- Dielectric loss

$$\gamma = \alpha_d + j\beta \rightarrow \alpha_d = \frac{k^2 \tan \delta}{2\beta} (NP/m) : \text{TE or TM case}$$

$$\alpha_d = \frac{k \tan \delta}{2} (NP/m) : \text{TEM case}$$

(derivation of the dielectric loss expression)

$$\text{wave eq. } \nabla^2 \bar{E} + k^2 \bar{E} = 0 \rightarrow (\nabla_{xy}^2 + \nabla_z^2) \bar{E} + k^2 \bar{E} = 0 \rightarrow \nabla_{xy}^2 \bar{E} + (\gamma^2 + k^2) \bar{E} = 0$$

$$\nabla_{xy}^2 \bar{E} + k_c^2 \bar{E} = 0, k_c^2 \equiv \gamma^2 + k^2$$

$$\rightarrow \gamma \equiv \alpha_d + j\beta = \sqrt{k_c^2 - k_d^2}$$

$$\therefore k_d = \omega \sqrt{\mu \epsilon} = \omega \sqrt{\mu(\epsilon' - j\epsilon'')} = \omega \sqrt{\mu \epsilon' (1 - j \tan \delta)} = k \sqrt{1 - j \tan \delta}$$

$$\tan \delta \equiv \frac{\epsilon''}{\epsilon'}, k = \omega \sqrt{\mu \epsilon'}$$

$$\rightarrow \gamma = \sqrt{k_c^2 - k^2 (1 - j \tan \delta)} = \sqrt{k_c^2 - k^2 + jk^2 \tan \delta}$$

$$\approx \sqrt{k_c^2 - k^2} + \frac{1}{2} \frac{j k^2 \tan \delta}{\sqrt{k_c^2 - k^2}} = j\beta + \frac{1}{2} \frac{k^2 \tan \delta}{\beta} = j\beta + \alpha_d$$

$$\Rightarrow \alpha_d = \frac{k^2 \tan \delta}{2\beta} (NP/m) : \text{TE or TM case}$$

$$\alpha_d = \frac{k \tan \delta}{2} (NP/m) : \text{TEM case} \because k_c = 0$$

3.5 Coaxial line

- TEM mode

$$\Phi(\rho, \theta) = \frac{\ln b/\rho}{\ln b/a} V_o$$

$$\bar{E}^+(\rho, \theta, z) = -\nabla_t \Phi(\rho, \theta) e^{-jkz} = \frac{V_o}{\ln b/a} e^{-jkz} \frac{\hat{\rho}}{\rho}$$

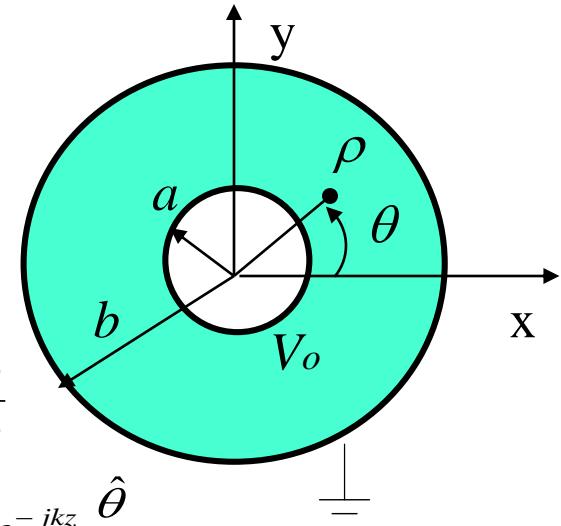
$$\bar{H}^+(\rho, \theta, z) = \frac{1}{Z_{TEM}} \hat{z} \times \bar{E}^+(\rho, \theta, z) = \frac{V_o}{\eta \ln b/a} e^{-jkz} \frac{\hat{\theta}}{\rho}$$

$$V^+(z) = \int_a^b \bar{E}^+(\rho, \theta, z) \bullet d\bar{l} = V_o e^{-jkz} \equiv V_o^+ e^{-jkz}$$

$$I^+(z) = \oint \bar{H}^+(\rho, \theta, z) \bullet d\bar{l} = \frac{2\pi V_o}{\eta \ln b/a} e^{-jkz} \equiv I_o^+ e^{-jkz}$$

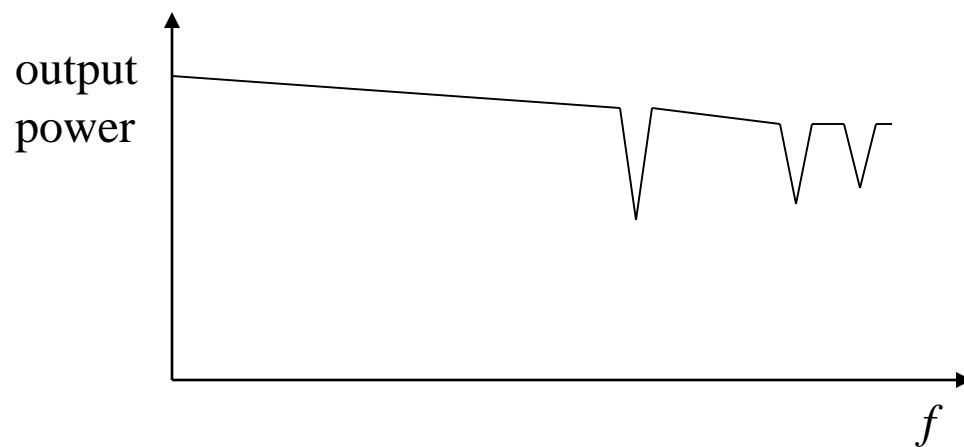
$$Z_o = \frac{V^+(z)}{I^+(z)} = \frac{\eta \ln b/a}{2\pi} = \frac{60}{\sqrt{\epsilon_r}} \ln \frac{b}{a} = \sqrt{\frac{L}{C}}, \beta = k = \omega \sqrt{\mu \epsilon}$$

$$L = \frac{\mu}{2\pi} \ln \frac{b}{a}, C = \frac{2\pi \epsilon}{\ln b/a} \quad (\text{Table 2.1, p.54})$$



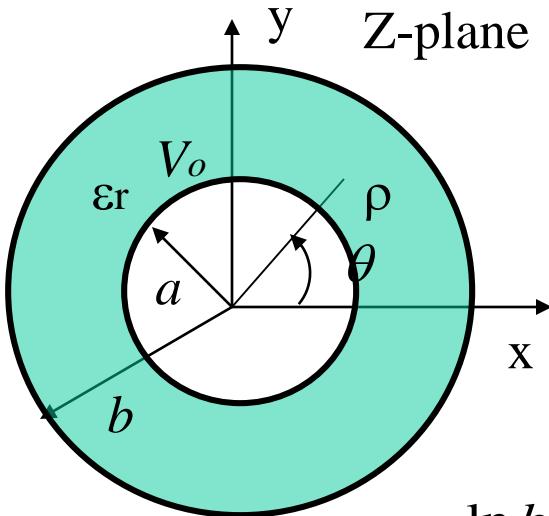
- Higher order mode effect

TE₁₁ mode (p.133 Fig.3.17) $f_{max} < f_c = \frac{1}{\pi(a+b)\sqrt{\mu\epsilon}}$



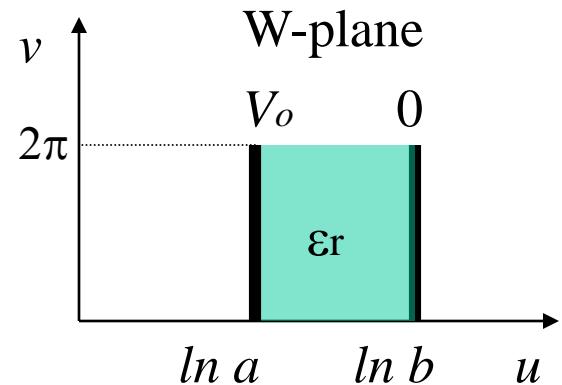
Discussion

1. Conformal mapping solution (Collin, *Field theory of guided waves*, p.262)



$$Z = x + jy$$

$$\begin{aligned} W &= \ln Z = \ln \rho e^{j\theta} \\ &= \ln \rho + j\theta \\ &= u + jv \end{aligned}$$



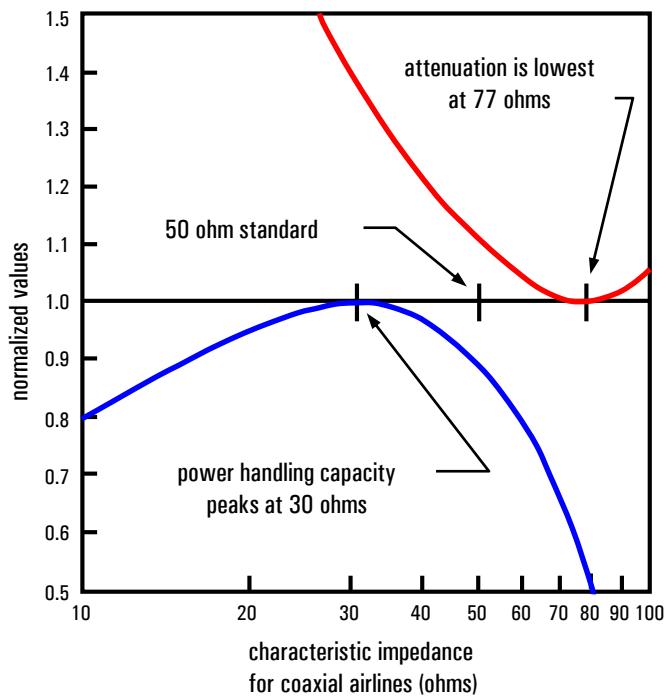
$$\Phi = \frac{\ln b - u}{\ln b - \ln a} V_o$$

$$W_e = \frac{1}{2} \epsilon \int_0^{2\pi} \int_{\ln a}^{\ln b} \left(\frac{\partial \Phi}{\partial u} \right)^2 + \left(\frac{\partial \Phi}{\partial v} \right)^2 du dv = \frac{\pi \epsilon V_o^2}{\ln b / a} = \frac{1}{2} C V_o^2$$

$$\Rightarrow C = \frac{2\pi \epsilon}{\ln b / a}, Z_o = \frac{1}{\nu_p C} = \frac{\sqrt{\mu \epsilon}}{C} = \frac{\eta}{2\pi} \ln \frac{b}{a}, \eta = \sqrt{\frac{\mu}{\epsilon}}$$

2. Reasons for selecting $Z_0=50\Omega$

Coaxial line has minimum attenuation as $Z_0=77\Omega$ (Prob. 2-27), and maximum power capacity as $Z_0=30\Omega$ (Prob. 3-28).

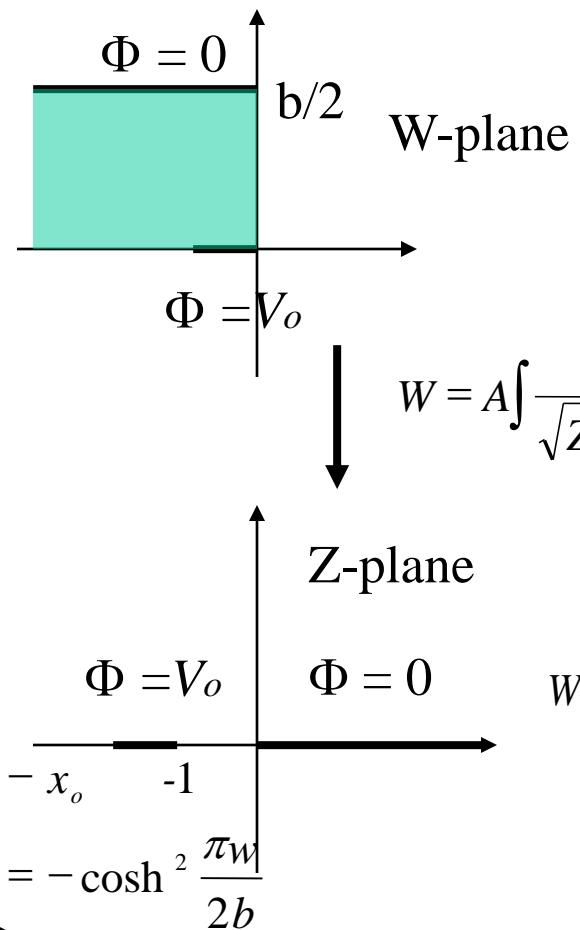


3. Types of coaxial connectors

type-N, SMA, APC3.5, APC2.4,..... (p.134, point of interest)

3.7 stripline

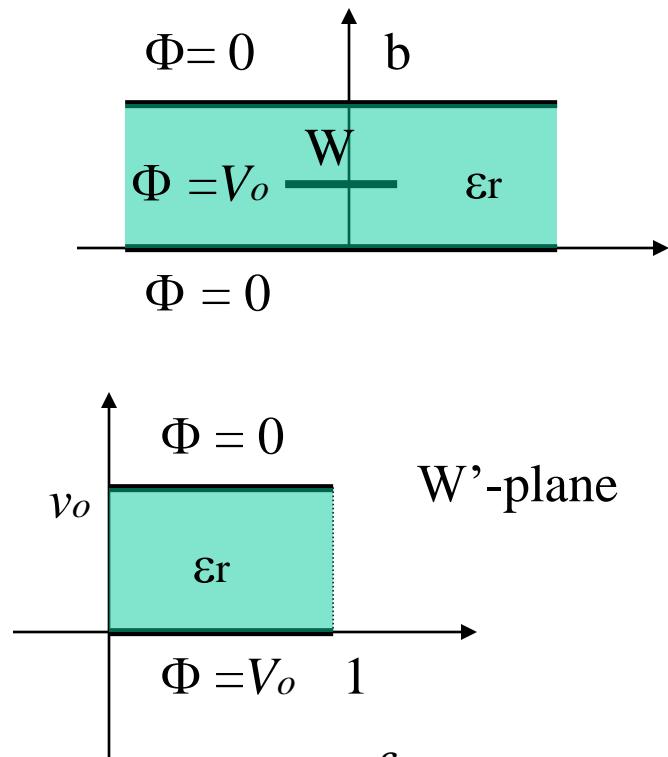
- Conformal mapping solution
(Collin's book, p.265)



$$W = A \int \frac{dZ}{\sqrt{Z(Z+1)}} + B$$

$$W' = A_l \int \frac{dZ}{\sqrt{Z(Z+x_o)(Z+1)}} + B_o$$

$$C = \frac{\epsilon}{\nu_o} \quad \rightarrow C = \frac{4\epsilon}{\nu_o}, \quad Z_o = \frac{\sqrt{\mu\epsilon}}{C}$$



- Electrostatic solution

$$\nabla_t^2 \Phi(x, y) = 0 \quad |x| < a/2, \quad 0 < y < b$$

$$B.C. \quad \Phi(x, y) = 0 \quad x = \pm a/2, \quad y = 0, b$$

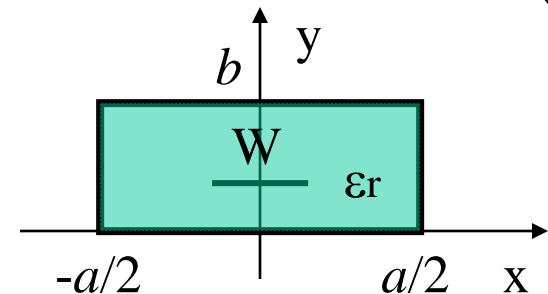
$$\Phi(x, y) = \begin{cases} \sum_{odd} A_n \cos \frac{n\pi}{a} x \sinh \frac{n\pi}{a} y & 0 \leq y \leq b/2 \\ \sum_{odd} A_n \cos \frac{n\pi}{a} x \sinh \frac{n\pi}{a} (b - y) & b/2 \leq y \leq b \end{cases}$$

$$E_y = -\frac{\partial \Phi}{\partial y} = \begin{cases} -\sum_{odd} A_n \left(\frac{n\pi}{a}\right) \cos \frac{n\pi}{a} x \cosh \frac{n\pi}{a} y & 0 \leq y \leq b/2 \\ \sum_{odd} A_n \left(\frac{n\pi}{a}\right) \cos \frac{n\pi}{a} x \cosh \frac{n\pi}{a} (b - y) & b/2 \leq y \leq b \end{cases}$$

$$\rho_s(x) = D_y(x, y = b^+/2) - D_y(x, y = b^-/2) \equiv \begin{cases} 1 & |x| < W/2 \\ 0 & |x| > W/2 \end{cases} \rightarrow A_n \dots (3.189)$$

$$V = - \int_0^{b/2} E_y(x = 0, y) dy = 2 \sum_{odd} A_n \sinh \frac{n\pi}{4a} b, \quad Q = \int_{-W/2}^{W/2} \rho_s(x) dx = W$$

$$\Rightarrow C = \frac{Q}{V} \dots (3.192), \quad Z_o = \sqrt{\frac{L}{C}} = \frac{1}{v_p C} = \frac{\sqrt{\epsilon_r}}{c C}$$



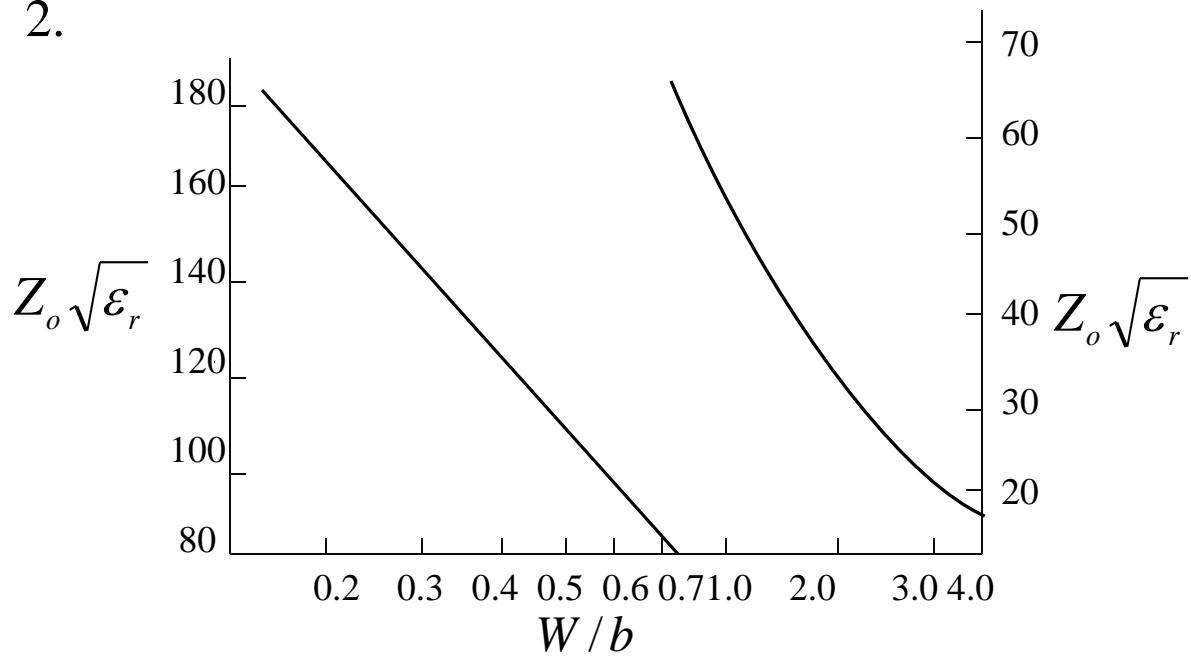
Discussion

1. analysis eq.(3.179) $W, b, \varepsilon \rightarrow Z_o$

synthesis eq.(3.180) $Z_o, b, \varepsilon \rightarrow W$

$$\alpha_d = \frac{k \tan \delta}{2}, \quad \alpha_c \text{ eq.(3.181)}$$

2.



3.8 Microstrip

- Characteristics

fabrication by printed circuit
devices can be bonded to strip
component are accessible

in-circuit characterization of devices is straightforward to implement
dc as well as ac signals can be transmitted

large variation in Z_0

$\alpha_c > \alpha_d$

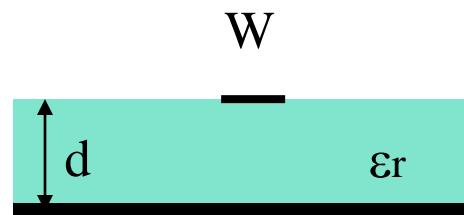
monolithic applications

structure is rugged and can withstand high voltages and power levels

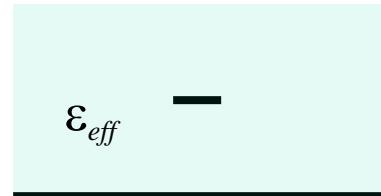
power handling is best with BeO substrate

used up to 300GHz or more

quasi-TEM mode for $d \ll \lambda$



- ϵ_{eff} concept



$$\text{TEM line } Z_o = \sqrt{\frac{L}{C}}, \nu_p = \frac{c}{\sqrt{\epsilon_r}}, \beta = \omega \sqrt{\mu \epsilon} = k_o \sqrt{\epsilon_r}, \lambda = \frac{\lambda_o}{\sqrt{\epsilon_r}}$$

$$\text{air filled microstrip (TEM line)} Z_{oa} = \sqrt{\frac{L}{C_a}} = \frac{1}{c C_a}$$

$$\text{microstrip (quasi-TEM line)} Z_o = \sqrt{\frac{L}{C}} = \frac{1}{\nu_p C}, \nu_p = \frac{1}{\sqrt{LC}} = \frac{c}{\sqrt{\epsilon_{\text{eff}}}}, \beta = k_o \sqrt{\epsilon_{\text{eff}}},$$

$$\lambda_g = \frac{\lambda_o}{\sqrt{\epsilon_{\text{eff}}}} \Rightarrow \frac{Z_o}{Z_{oa}} = \sqrt{\frac{C_a}{C}} = \frac{1}{\sqrt{\epsilon_{\text{eff}}}}, \frac{C}{C_a} = \left(\frac{c}{\nu_p}\right)^2 \equiv \epsilon_{\text{eff}}$$



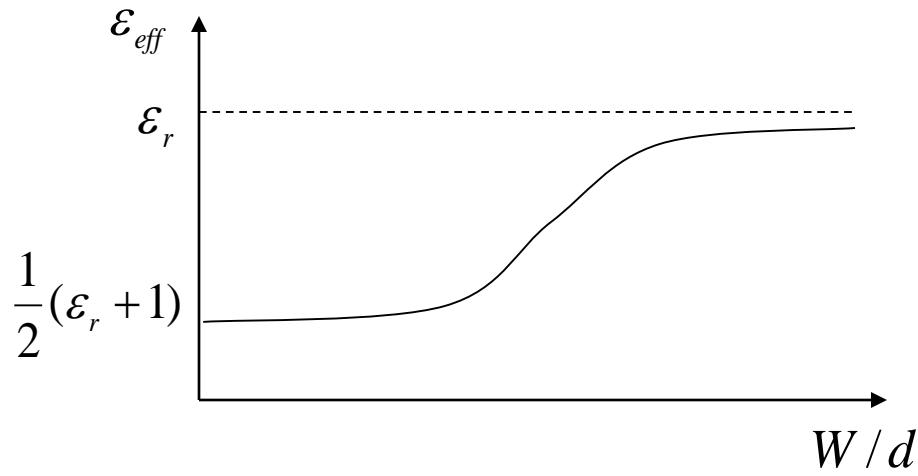
$$\epsilon_{eff} \rightarrow \frac{1}{2}(\epsilon_r + 1)$$

$$\epsilon_{eff} \rightarrow \epsilon_r$$

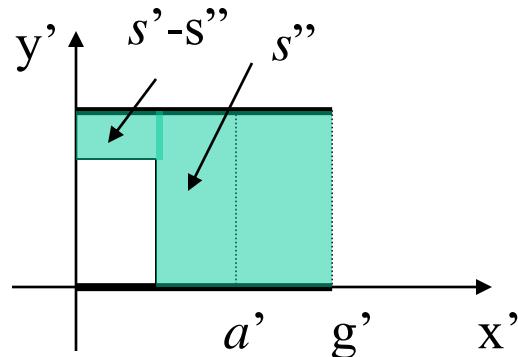
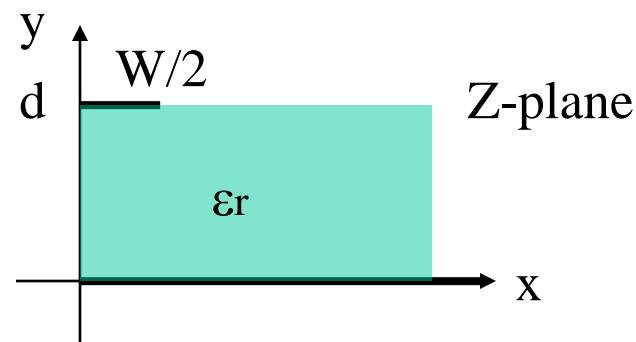
$$\frac{1}{2}(\epsilon_r + 1) \leq \epsilon_{eff} \leq \epsilon_r$$

filling factor q

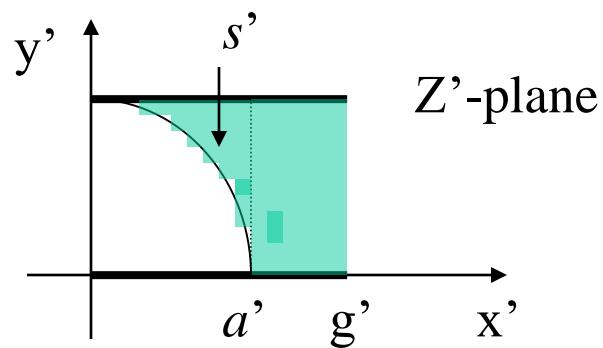
$$\epsilon_{eff} = q\epsilon_r + (1-q)1 = 1 + q(\epsilon_r - 1), \quad \frac{1}{2} \leq q \leq 1$$



- Conformal mapping solution (Gupta, Garg and Bahl, *Microstrip lines and slotlines*, p.9)



$$Z = j\pi + d \tanh \frac{Z'}{2} - Z'$$



$$s = s'' + \frac{s' - s''}{\epsilon_r}$$

$$q = \frac{g' - a' + s}{g'}$$

- Electrostatic solution

$$\nabla_t^2 \Phi(x, y) = 0 \quad |x| \leq a/2, \quad 0 \leq y < \infty$$

$$B.C. \quad \Phi(x, y) = 0 \quad x = \pm a/2, \quad y = 0, \infty$$

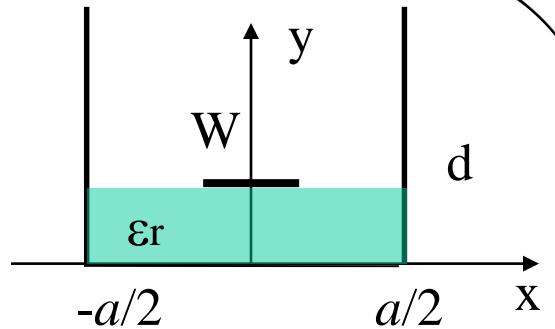
$$\Phi(x, y) = \begin{cases} \sum_{odd} A_n \cos \frac{n\pi}{a} x \sinh \frac{n\pi}{a} y & 0 \leq y < d \\ \sum_{odd} A_n \cos \frac{n\pi}{a} x \sinh \frac{n\pi}{a} d e^{-n\pi(y-d)/a} & d \leq y < \infty \end{cases}$$

$$E_y = -\frac{\partial \Phi}{\partial y} = \begin{cases} -\sum_{odd} A_n \left(\frac{n\pi}{a}\right) \cos \frac{n\pi}{a} x \cosh \frac{n\pi}{a} y & 0 \leq y < d \\ \sum_{odd} A_n \left(\frac{n\pi}{a}\right) \cos \frac{n\pi}{a} x \sinh \frac{n\pi}{a} d e^{-n\pi(y-d)/a} & d \leq y < \infty \end{cases}$$

$$\rho_s(x) = D_y(x, y = d^+) - D_y(x, y = d^-) = \epsilon_o E_y(x, y = d^+) - \epsilon_o \epsilon_r E_y(x, y = d^-) \cong \begin{cases} 1 & |x| < W/2 \\ 0 & |x| > W/2 \end{cases} \rightarrow A_n$$

$$V = - \int_0^d E_y(x = 0, y) dy = \sum_{odd} A_n \sinh \frac{n\pi}{a} d, \quad Q = \int_{-W/2}^{W/2} \rho_s(x) dx = W$$

$$\Rightarrow C = \frac{Q}{V}, \quad \epsilon_{eff} = \frac{C}{C_a}, \quad Z_o = \sqrt{\frac{L}{C}} = \frac{1}{v_p C} = \frac{\sqrt{\epsilon_{eff}}}{c C}$$



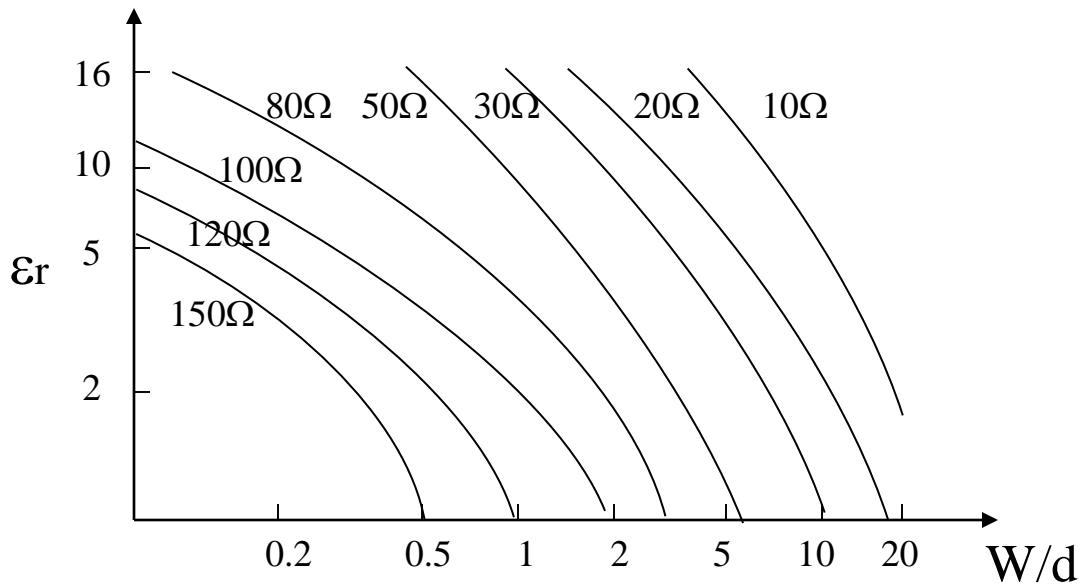
Discussion

1. analysis eq.(3.196, 195) $W, d, \varepsilon \rightarrow Z_o, \varepsilon_{eff}$

synthesis eq.(3.197, 195) $Z_o, d, \varepsilon \rightarrow W, \varepsilon_{eff}$

$$\alpha_d = \frac{k_o \varepsilon_r (\varepsilon_{eff} - 1) \tan \delta}{2 \sqrt{\varepsilon_{eff} (\varepsilon_r - 1)}} \quad (3.198), \quad \alpha_c = \frac{R_s}{Z_o W} \quad (3.199)$$

2.



(derivation of eq.(3.198))

$$\text{TEM line } \alpha_d = \frac{k \tan \delta}{2} = \frac{k_o \sqrt{\epsilon_r} \tan \delta}{2}$$

microstrip line:

$$(1) \epsilon_{eff} = q\epsilon_r + (1-q) = q(\epsilon_r - 1) + 1 \rightarrow q = \frac{\epsilon_{eff} - 1}{\epsilon_r - 1}$$

$$(2) \sqrt{\epsilon_r} \rightarrow \sqrt{\epsilon_{eff}}$$

$$(3) \tan \delta \rightarrow \tan \delta_{eff} = \frac{\epsilon''_{eff}}{\epsilon_{eff}}, \epsilon''_{eff} = q\epsilon'' + 0(1-q) = q\epsilon''$$

$$\alpha_d = \frac{k_o \sqrt{\epsilon_{eff}} \tan \delta_{eff}}{2} = \frac{k_o \sqrt{\epsilon_{eff}}}{2} \frac{q\epsilon''}{\epsilon_{eff}} = \frac{k_o q \epsilon''}{2 \sqrt{\epsilon_{eff}}} = \frac{k_o q}{2 \sqrt{\epsilon_{eff}}} \frac{\epsilon''}{\epsilon_r} \epsilon_r$$

$$= \frac{k_o}{2 \sqrt{\epsilon_{eff}}} \frac{\epsilon_{eff} - 1}{\epsilon_r - 1} \tan \delta \epsilon_r = \frac{k_o \epsilon_r \tan \delta}{2 \sqrt{\epsilon_{eff}}} \frac{\epsilon_{eff} - 1}{\epsilon_r - 1}$$

4. substrate material

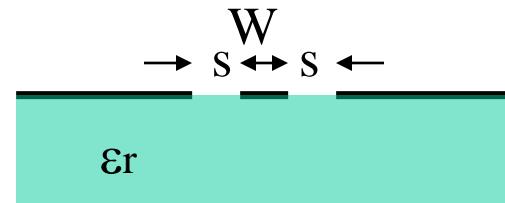
	ϵ_r	$\tan\delta$ @10GHz	conductor material		
			R_s ($\Omega/\text{sq} \times 10^{-7} \sqrt{f}$)	δ_s (um)@2GHz	
GaAs	12.9	0.002	Ag	2.5	1.4
Al_2O_3 (99.5%)	10.1 ± 0.25	0.0002	Cu	2.6	1.5
quartz	3.8	0.0001	Au	3.0	1.7
RT/duroid 5880	2.2 ± 0.02	0.0009	Al	3.3	1.9
RT/duroid 6006	6.15 ± 0.15	0.0027	Cr	4.7	2.7
BeO	6.8	0.0003	Ta	7.2	4.0
FR4 (G-10)	4-4.6	0.018-0.025			
Si	11.7	0.005	1 oz Cu \rightarrow 1.4 mil (35 um) thickness		
$^* \text{SiO}_2$	4				
$^* \text{Si}_3\text{N}_4$	7.6 (vapor phase) 6.5 (sputtering)		skin depth $\delta_s = \sqrt{\frac{2}{\omega\mu\sigma}}$		

* : MIM capacitor



3.11 Summary of transmission lines and waveguides

- comparison of coaxial line, stripline and microstrip, (p.158, Table 3.6)
- CPW (coplanar waveguide)
 - fabrication easy
 - quasi-TEM operation
 - radiation problem when gap width approaches $\lambda/2$
 - monolithic applications
 - less radiation than microstrip if well-balanced
 - higher order modes (coupled slot mode)
- www.appwave.com for computer assisted transmission line analysis



Solved Problems

Prob. 3.28 Find Z_o of a coaxial line to have maximum power capacity

$$\text{breakdown field strength of air } E_d = 3 \times 10^6 \text{ V/m} = \frac{V_o}{\rho \ln \frac{b}{a}} \rightarrow V_{\max} = E_d a \ln \frac{b}{a}$$

$$\text{maximum power capacity } P_{\max} = \frac{1}{2} \frac{V_{\max}^2}{Z_o}, Z_o = \frac{\eta_o}{2\pi} \ln \frac{b}{a} \rightarrow P_{\max} = \frac{\pi a^2 E_d^2}{\eta_o} \ln \frac{b}{a}$$

$$\frac{dP_{\max}}{da} = 0 \rightarrow \ln \frac{b}{a} = \frac{1}{2} \Rightarrow Z_o = \frac{\eta_o}{2\pi} \ln \frac{b}{a} = \frac{377}{2\pi} \frac{1}{2} \approx 30 \Omega$$

ADS examples: Ch3_prj